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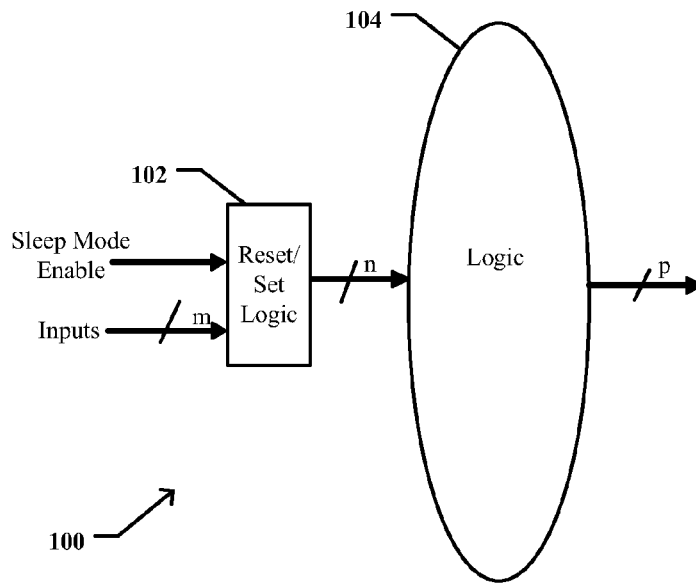


FIGURE 1

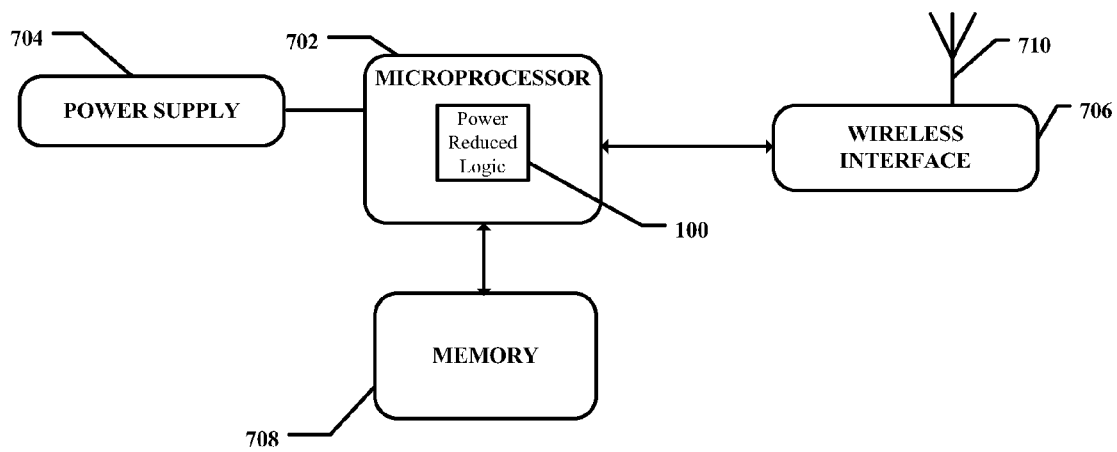
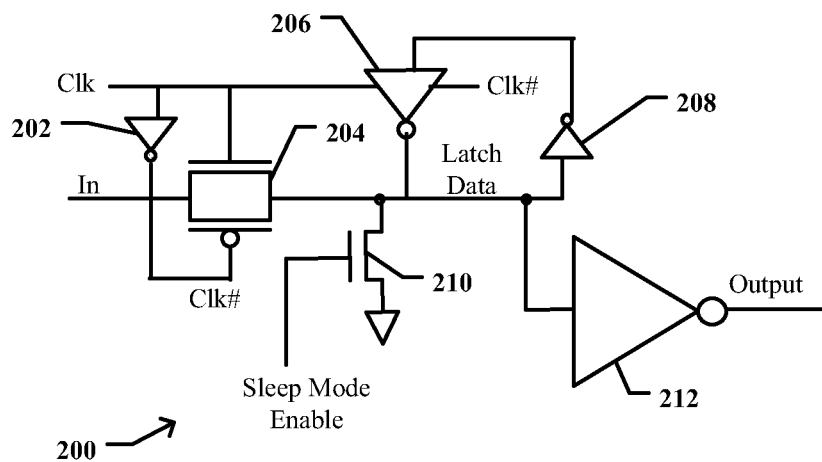
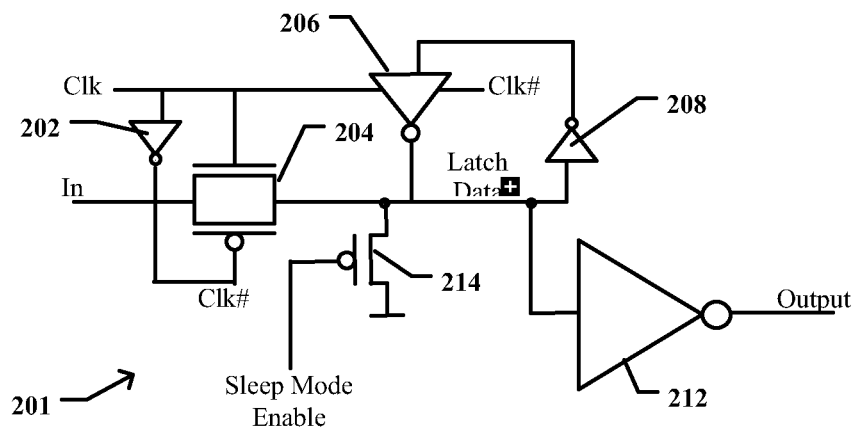


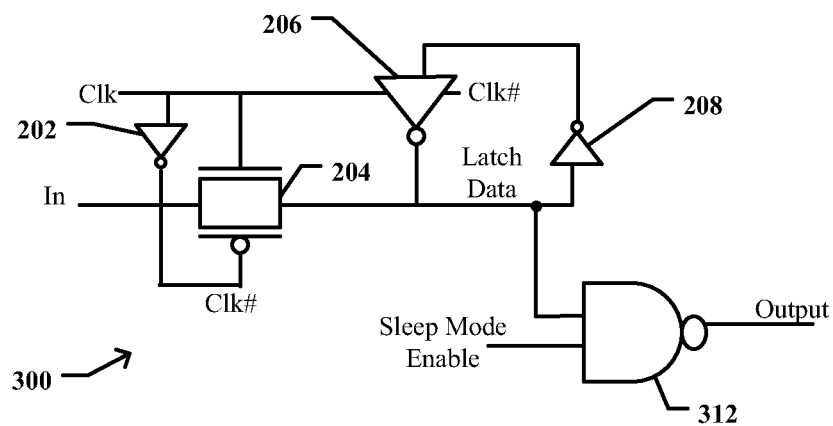
FIGURE 7



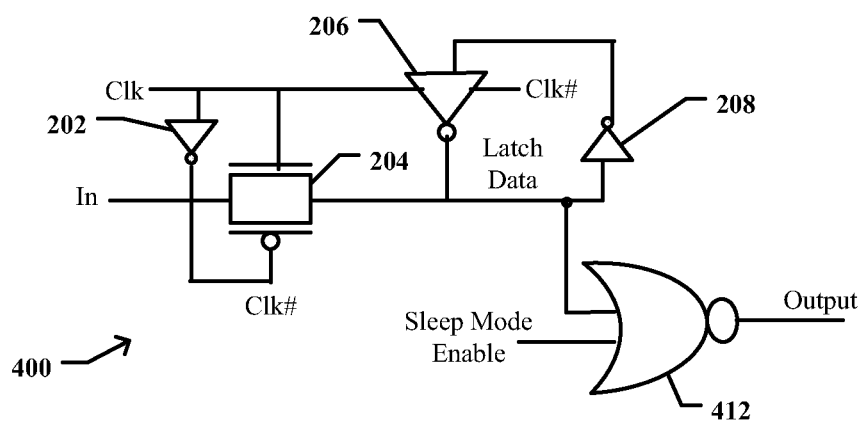
**FIGURE 2A**  
(Prior Art)



**FIGURE 2B**  
(Prior Art)



### FIGURE 3



## FIGURE 4

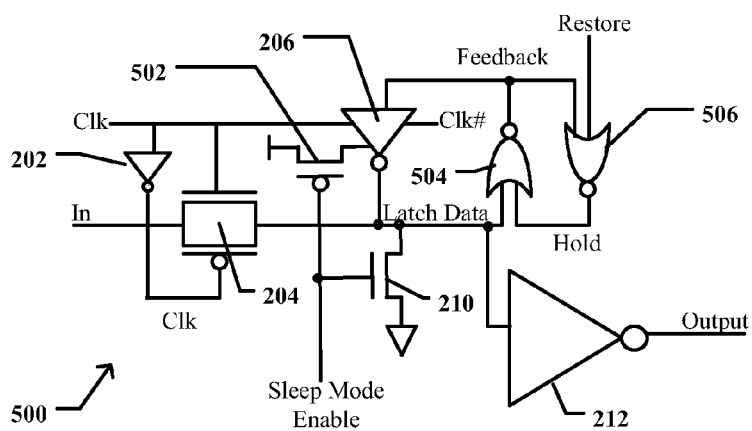


FIGURE 5A

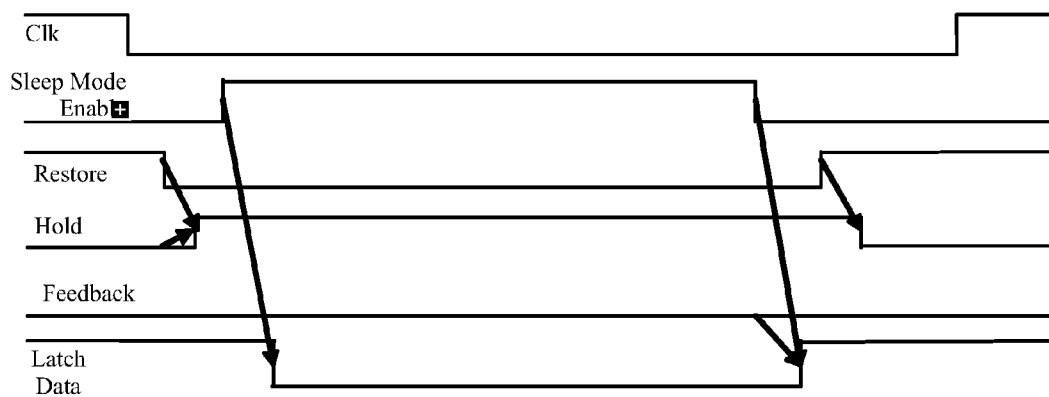


FIGURE 5B

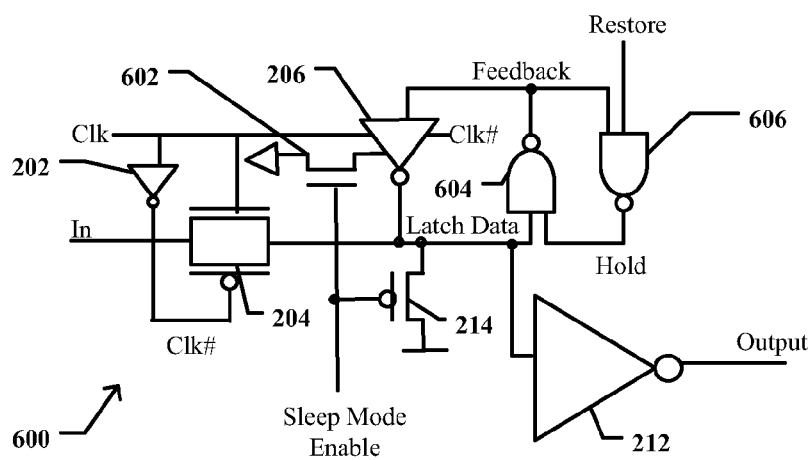


FIGURE 6A

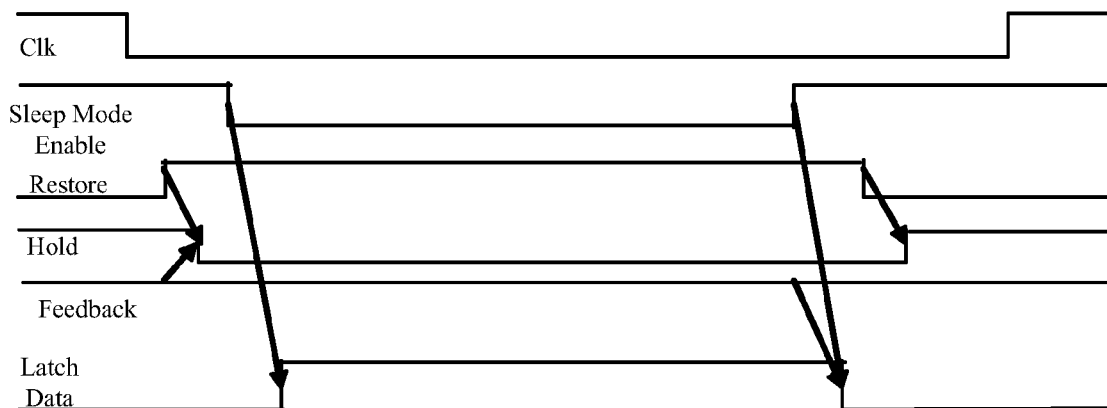


FIGURE 6B

1

# POWER REDUCING LOGIC AND NON-DESTRUCTIVE LATCH CIRCUITS AND APPLICATIONS

## CROSS REFERENCE TO RELATED APPLICATIONS

This application is a continuation of and claims priority to pending U.S. patent application Ser. No. 12/847,248, filed on Jul. 30, 2010, and entitled, "POWER REDUCING LOGIC AND NON-DESTRUCTIVE LATCH CIRCUITS AND APPLICATIONS" which claims priority to pending U.S. patent application Ser. No. 11/270,912, filed on Nov. 10, 2005, and entitled, "POWER REDUCING LOGIC AND NON-DESTRUCTIVE LATCH CIRCUITS AND APPLICATIONS." This application is entirely incorporated by reference.

## BACKGROUND

Large scale integrated circuit chips such as microprocessors use circuits such as sequential logic circuits to implement many different types of logic functions. (As used herein, the term "chip," or die, refers to a piece of a material, such as a semiconductor material, that includes a circuit such as an integrated circuit or a part of an integrated circuit.) It is becoming ever more important to save power in chips, for example, with mobile applications or in other relatively low power environments. Unfortunately, as integrated circuits become larger and greater performance demands are placed on the chips, it is becoming even more difficult to reduce power consumption.

## BRIEF DESCRIPTION OF THE DRAWINGS

Embodiments of the invention are illustrated by way of example, and not by way of limitation, in the figures of the accompanying drawings in which like reference numerals refer to similar elements.

FIG. 1 is a block diagram of logic circuitry with a power reducing sleep mode feature according to some embodiments.

FIG. 2A is a schematic diagram of a conventional set latch circuit.

FIG. 2B is a schematic diagram of a conventional reset latch circuit.

FIG. 3 is a schematic diagram of a non-destructive set latch in accordance with some embodiments.

FIG. 4 is a schematic diagram of a non-destructive reset latch in accordance with some embodiments.

FIG. 5A is a schematic diagram of a non-destructive set latch in accordance with some embodiments.

FIG. 5B is a timing diagram illustrating the operation of the circuit of FIG. 5A in accordance with some embodiments.

FIG. 6A is a schematic diagram of a non-destructive reset latch in accordance with some embodiments.

FIG. 6B is a timing diagram illustrating the operation of the circuit of FIG. 6A in accordance with some embodiments.

FIG. 7 is a block diagram of a computer system with at least one logic circuit with a power reducing feature in accordance with some embodiments.

## DETAILED DESCRIPTION

FIG. 1 is a block diagram showing logic circuits having a sleep mode feature in accordance with some embodiments

2

disclosed herein. As indicated, reset/set latch circuitry **102** is coupled to logic circuits within logic circuitry **104** to provide operating inputs when the circuitry is in operation and to set or reset the logic circuits to known, sleep mode states when in a sleep mode. The sleep mode is entered with the assertion of the Sleep Mode Enable signal, which may actually comprise one or more signals that may be asserted Low and/or High. (It should be appreciated that a set or a reset latch may include any latch circuit that is capable of outputting a known logic value in response to an asserted control signal. Typically, the control input is referred to as an R or an S input, however in this disclosure, it is referred to as a Sleep Mode Enable signal.)

When a sleep mode is entered, inputs to the logic circuits are set or reset so that they consume reduced overall leakage power. The logic circuits can comprise numerous gates (e.g., NAND, NOR) that even though not being operated, may consume different amounts of leakage power depending upon their inputs. For example, a n-input NAND gate (e.g., implemented with PMOS devices) with inputs being all High may have less leakage (e.g., about ten times) than with its inputs all being Low. Thus, during a sleep mode, it is desirable to set such NAND gate inputs High. On the other hand, other gates (e.g., n-input PMOS NOR gates) may leak less with their inputs all being Low. Thus, with such gates, it would be desirable to reset their inputs Low. (The term "PMOS transistor" refers to a P-type metal oxide semiconductor field effect transistor. Likewise, "NMOS transistor" refers to N-type metal oxide semiconductor field effect transistor. It should be appreciated that whenever the terms: "transistor", "MOS transistor", "NMOS transistor", or "PMOS transistor" are used, unless otherwise expressly indicated or dictated by the nature of their use, they are being used in an exemplary manner. They encompass the different varieties of MOS devices including devices with different VTs and oxide thicknesses to mention just a few. Moreover, unless specifically referred to as MOS or the like, the term transistor can include other suitable transistor types, e.g., junction-field-effect transistors, bipolar-junction transistors, and various types of three dimensional transistors, known today or not yet developed.)

It may not be possible to so set or reset the inputs for all of the gates in logic block **104** during a sleep mode, but at least some may be set/reset to reduce the overall leakage. In some embodiments, e.g., during a design phase, the topology and/or circuit style may be changed, for example, by using DeMorgan's theorem to replace NAND with NOR gates or vice versa so that in the sleep mode, even lower leakage, given available input combinations, may be achieved. Notwithstanding the fact that the reset/set latch circuits **102** are shown as all being "ahead" of the logic block **104**, in some embodiments, reset and set circuits may also (or otherwise) be disposed within the logic block **104** to allow for more gate inputs to be suitably set or reset to attain possibly better leakage reduction.

When the logic block **104** is being operated (not in a sleep mode), the "Sleep Mode Enable" signal is de-asserted, and the R/S latches **102** operate as normal latches coupling input data to the logic circuitry **104**. Conversely, upon entrance of a sleep mode, the "Sleep Mode Enable" signal(s) is asserted causing the set/reset latches **102** to set or reset logic circuit inputs, which causes them to enter the reduced leakage states. In some embodiments, non-destructive reset and/or set latch circuits (for which some embodiments are disclosed below) are utilized so that when the logic block **104** is to



3

come out of the sleep mode, the set/reset circuits **102** can return the logic circuit inputs to their operating states when the sleep mode was entered.

FIG. **2A** shows a conventional, destructive set latch **200**, which may be used to implement some of the set latch circuits discussed above. Set latch **200** comprises inverters **202**, **208**, and **212**, pass gate **204**, tri-state inverter **206**, and an NMOS transistor **210**, coupled together as indicated. When the circuit is not in a sleep mode (the sleep mode enable signal is de-asserted Low), the circuit operates as a latch. When the clock (Clk) is High, the passgate **204** turns on (passing the input (In) value to the “Latch Data” node, and the tri-state inverter **206** is in a tri-state mode (which allows the Latch Data node value to change). Conversely, when the clock is Low, the passgate **204** turns off, and the tri-state inverter **206** turns on, acting as an inverter, to hold (or latch) the Latch Data node value. Thus, upon a High to Low clock transition, the input (In) value is “latched” at the Latch Data node. The latch output (Output) is at the output of inverter **212**, which buffers and inverts the value at the Latch Data node. When a sleep mode is entered, the Sleep Mode Enable input asserts (goes High), causing the Latch Data node to go Low and the latch output (Out) to go High (or to set). (Note that the inverter **212** will typically be suitably larger than the other inverters to sufficiently drive the output signal. Likewise, depending on the operation of tri-state inverter **206**, e.g., the clock may be deactivated during a sleep mode, the transistor **210** should be sufficient to pull down the Latch Data node upon entry into a sleep mode.)

FIG. **2B** shows a conventional reset latch circuit **201**, which may be suitable for implementing one or more of the reset circuits in the reset/set circuitry **102**. Reset latch **201** is the same as Set latch **200** except that it includes a PMOS transistor **214** (instead of an NMOS transistor **210**) coupling the Latch Data node to a High supply (e.g., VCC) instead of to a Low reference (e.g., ground). Thus, with the reset circuit, the Sleep Mode Enable signal is asserted when it is Low and when entered, it causes the Latch Data node to go High, which causes the output to go Low (or reset).

FIG. **3** shows a novel non-destructive set latch circuit **300** according to some embodiments. Set latch **300** may be used, for example, for one or more of the set circuits in set/reset circuitry **102**. In some embodiments, it may be desired since it does not lose the value at the Latch Data node when entering a sleep mode. Set latch **300** is generally similar to set latch **200** except that it includes NAND gate **312** in place of transistor **210** and output inverter **212**. The sleep mode is entered by asserting (Low) the Sleep Mode Enable signal, which causes the output of NAND gate **312** to go High, regardless of the value at the Latch Data node. On the other hand, when the Sleep Mode Enable signal is de-asserted (High), the circuit acts as a latch. (Note that in the depicted embodiment, the clock is kept Low during a sleep mode to maintain the value at the Latch Data node. In other embodiments, this may not be the same or necessary.)

FIG. **4** shows a novel non-destructive reset latch circuit **400** according to some embodiments. Reset latch **400** may be used, for example, for one or more of the reset circuits in set/reset circuitry **102**. In some embodiments, it may be desired since it does not lose the value at the Latch Data node when entering a sleep mode. Reset latch **400** is generally similar to reset latch **201** except that it includes NOR gate **412** in place of sleep mode, pull-up transistor **214** and output inverter **212**. The sleep mode is entered by asserting (High) the Sleep Mode Enable signal, which causes the output of NOR gate **412** to go Low, regardless of

4

the value at the Latch Data node. On the other hand, when the Sleep Mode Enable signal is de-asserted (Low), the circuit acts as a latch. (Again, in the depicted embodiment, the clock is kept Low during a sleep mode to maintain the value at the Latch Data node. In other embodiments, this may not be the same or necessary.)

With reference to FIGS. **5A** and **5B**, a novel, non-destructive set latch **500** (FIG. **5A**) and a corresponding timing diagram (FIG. **5B**) illustrating its operation in accordance with some embodiments, are shown. The set latch **500** is similar to set latch **200** except that it incorporates a restore circuit (formed from cross-coupled NOR gates **504** and **506**) to store the Latch Data node value during a sleep mode. (As used herein, a restore circuit may comprise any suitable combination of gates and/or other devices to store the value from the Latch Data node during a sleep mode and provide it back to the Latch Data node when the sleep mode is departed.) Latch circuit **500** also includes a transistor **502** to controllably disable a supply reference (VCC) to the tri-state inverter **206** during the sleep mode. It may be appreciated that in this embodiment, inverter **212** is used as the output driving gate instead of a NAND gate (as with set latch **300**), which may make it better suited for some applications, e.g., where greater output drive capability is desired.

When the set latch **500** operates in a latch mode (not sleep mode), the Restore and Sleep Mode Enable signals are de-asserted (Restore is High and Sleep Mode Enable is Low). When the Sleep Mode Enable signal is de-asserted (Low), transistor **502** turns off (allowing the Latch Data node to carry the input, In, value), while transistor **502** turns on to turn on the tri-state inverter **206**. The Restore signal being de-asserted (High) causes a Low at the output of NOR gate **506**, which causes NOR gate **504** to act as an inverter with the State value as its input. Thus, when not in the sleep mode, latch circuit **500** essentially operates like latch circuit **200** when latch circuit **200** is not in a sleep mode.

As seen in FIG. **5B**, when the sleep mode is entered, the Restore signal is asserted (Low). This causes the Latch Data node value to be stored in the restore circuit (cross-coupled NOR gates **504**, **506**). This is followed by the assertion of the Sleep Mode Enable signal (High), which turns off the tri-state inverter **206** and pulls down the Latch Data node thereby “setting” the Output High.

When the latch **500** is to depart from the sleep mode, the Sleep Mode Enable signal is de-asserted (Low) turning on the tri-state inverter **206**, while at the same time, turning off transistor **502** thereby causing the Latch Data node value to be at its value at the time the sleep mode was entered. The Restore signal is then de-asserted (High), and the circuit once again (depending on the Clk signal) can function as a latch.

With reference to FIGS. **6A** and **6B**, a novel, non-destructive reset latch **600** (FIG. **6A**) and a corresponding timing diagram (FIG. **6B**) illustrating its operation in accordance with some embodiments, are shown. It is similar to set latch **500** except in the following respects. It is a reset latch, so when the sleep mode is entered, the Output is Low instead of High. In addition, its restore circuit is formed from cross-coupled NAND gates **604**, **606** (rather than NOR gates), its sleep mode transistor **214** is a PMOS device rather than an NMOS device, and its supply reference transistor **602** is an NMOS device controllably coupling a ground reference to the tri-state inverter **206** rather than a PMOS device coupling a VCC supply. Accordingly, the Sleep Mode Enable signal is de-asserted when it is High, and the Restore signal is de-asserted when Low.

5

Thus, as shown in the timing diagram of FIG. 6B, when the Sleep Mode Enable signal is de-asserted (High) and the Restore signal is de-asserted (Low), latch 600 operates as a latch. When the sleep mode is entered, the Restore signal is asserted (High) to store the value at the Latch Data node in the restore circuit (NAND gates 604, 606), and the Sleep Mode Enable signal is subsequently asserted (Low) to enter the sleep mode and cause the Output to go Low. When coming out of the sleep mode, the Sleep Mode Enable signal is de-asserted (High), and the Restore signal is then de-asserted (Low) to place the Latch Data node at its value when the sleep mode was entered.

With reference to FIG. 7, one example of a computer system is shown. The depicted system generally comprises a processor 702 that is coupled to a power supply 704, a wireless interface 706, and memory 708. It is coupled to the power supply 704 to receive from it power when in operation. The wireless interface 706 is coupled to an antenna 410 to communicatively link the processor through the wireless interface chip 706 to a wireless network (not shown). Microprocessor 702 comprises a power reduced logic block 100, in accordance with embodiments described above, comprising a variety of logic circuits that are controlled to enter known power-reducing states during a sleep mode.

It should be noted that the depicted system could be implemented in different forms. That is, it could be implemented in a single chip module, a circuit board, or a chassis having multiple circuit boards. Similarly, it could constitute one or more complete computers or alternatively, it could constitute a component useful within a computing system.

The invention is not limited to the embodiments described, but can be practiced with modification and alteration within the spirit and scope of the appended claims. For example, it should be appreciated that the present invention is applicable for use with all types of semiconductor integrated circuit ("IC") chips. Examples of these IC chips include but are not limited to processors, controllers, chip set components, programmable logic arrays (PLA), memory chips, network chips, and the like.

Moreover, it should be appreciated that example sizes/models/values/ranges may have been given, although the present invention is not limited to the same. As manufacturing techniques (e.g., photolithography) mature over time, it is expected that devices of smaller size could be manufactured. In addition, well known power/ground connections to IC chips and other components may or may not be shown within the FIGS. for simplicity of illustration and discussion, and so as not to obscure the invention. Further, arrangements may be shown in block diagram form in order to avoid obscuring the invention, and also in view of the fact that specifics with respect to implementation of such block diagram arrangements are highly dependent upon the platform within which the present invention is to be implemented, i.e., such specifics should be well within purview of one skilled in the art. Where specific details (e.g., circuits) are set forth in order to describe example embodiments of the invention, it should be apparent to one skilled in the art that the invention can be practiced without, or with variation of, these specific details. The description is thus to be regarded as illustrative instead of limiting.

What is claimed is:

1. A chip, comprising:

a non-destructive sequential unit with restore function, the non-destructive sequential unit having an output node, wherein the restore function allows the non-destructive

6

sequential unit to return logic state on the output node to a state which was on the output node before a sleep mode was entered; and

a sleep enabled combinational logic element having a first input coupled to the non-destructive sequential unit output node and a second input to control entry into one of the sleep mode and an operational mode,

the sleep enabled combinational logic element having an output node to be at a predetermined logic state to reduce downstream circuit leakage during the sleep mode and to be at a logic value that is determined by an output on the non-destructive sequential unit output node during the operational mode.

2. The chip of claim 1, in which the sleep enabled combinational logic element comprises a NOR gate, with the predetermined sleep mode logic state being a logic '0.

3. The chip of claim 1, in which the sleep enabled combinational logic element comprises a NAND gate, with the predetermined sleep mode logic state being a logic '1.

4. The chip of claim 1, in which the non-destructive sequential unit includes a cross-coupled gate circuit to store a data state during the sleep mode.

5. The chip of claim 4, in which the cross-coupled gate circuit includes a cross-coupled inverter pair.

6. The chip of claim 1, wherein the non-destructive sequential unit includes a transistor to controllably disable a supply to a device during the sleep mode.

7. The chip of claim 6, wherein the transistor is a p-type transistor and the supply is a power supply.

8. The chip of claim 6, wherein the transistor is an n-type transistor and the supply is a ground supply.

9. The chip of claim 1, wherein the restore function is implemented by a restore signal received by a NAND logic gate or a NOR logic gate.

10. An apparatus, comprising:

a processor comprising a logical block configured to be in one of at least a sleep mode and an operational mode, the logical block having a plurality of non-destructive sequential units with restore function, each with an output coupled to a separate, associated sleep enabled combinational logic element, wherein the restore function allows the non-destructive sequential units to return logic state on their output nodes to a state which was on the output nodes before the sleep mode was entered,

wherein at least one of the sleep enabled combinational logic element has:

an input to control entry into the sleep and operational modes, and

an output node to be at a predetermined logic state to reduce downstream circuit leakage during the sleep mode and to be at a logic value that is determined by the output of one of the non-destructive sequential units during the operational mode,

wherein outputs of the non-destructive sequential units with restore function, during the sleep mode, constitute a sleep mode output bus, defining a predetermined combination of logic values to reduce downstream leakage during the sleep mode.

11. The apparatus of claim 10, in which the plurality of sleep enabled combinational logic elements comprise NOR and NAND gates to provide the predetermined combination of logic values.

12. The apparatus of claim 10, in which the plurality of non-destructive sequential units each include a cross-coupled gate circuit to store a data state during the sleep mode.

7

13. The apparatus of claim 12, in which the cross-coupled gate circuits include cross-coupled inverter pairs.

14. The apparatus of claim 12, in which the cross-coupled gate circuits include cross-coupled NOR gate pairs.

15. A mobile device, comprising

a processor comprising a logic circuit having:

a plurality of circuit elements with inputs, and

one or more clocked, non-destructive latch circuits with

restore function, the non-destructive latch circuits

coupled to the inputs to provide operational data for

an operational mode and to cause at least some of the

inputs to be at preselected values resulting in reduced

leakage during a sleep mode, wherein the restore

function allows the non-destructive latch circuits to

return logic state on their respective output node to

a state which was on the output node before the sleep

mode was entered; and

a radio with an antenna coupled to a wireless interface

of the processor to wirelessly couple the processor to

a wireless network.

16. The mobile device of claim 15, in which the logic

circuit comprises one or more sequential logic circuits.

17. The mobile device of claim 15, in which the non-

destructive latch circuits each comprise a sequential unit and

a sleep enabled combinational logic gate at an output of the

sequential unit.

18. The mobile device of claim 17, in which the non-

destructive latch circuits each comprise a cross-coupled gate

to store a data bit during the sleep mode.

19. The mobile device of claim 17, in which the sleep

enabled combinational logic gates comprise NAND and

NOR gates to provide, respectively, logic '1s and '0s during

the sleep mode.

8

20. A mobile system, comprising:

a processor comprising a logic; and

a radio coupled to a wireless interface of the processor to

wirelessly couple the processor to a wireless network,

the radio comprising a controller with a logical block

configured to be in one of at least a sleep mode and an

operational mode, the logical block having a plurality

of non-destructive sequential units with restore func-

tion, each with an output coupled to a separate, asso-

ciated sleep enabled combinational logic element,

wherein the restore function allows the non-destructive

sequential units to return logic state on their respective

output node to a state which was on the output node

before the sleep mode was entered,

wherein at least one of the sleep enabled combinational

logic element has:

an input to control entry into the sleep and operational

modes, and

an output node to be at a predetermined logic state to

reduce downstream circuit leakage during the sleep

mode and to be at a logic value that is determined by

the output of the non-destructive sequential unit during

the operational mode.

21. The mobile system of claim 20, in which the sleep

enabled combinational logic elements comprise NOR and

NAND gates to provide the predetermined combination of

logic values.

22. The mobile system claim 20, in which the non-

destructive sequential units each include a cross-coupled

gate circuit to store a data state during the sleep mode.

23. The mobile system of claim 22, in which the cross-

coupled gate circuits include cross-coupled inverter pairs.

24. The mobile system of claim 22, in which the cross-

coupled gate circuits include cross-coupled NOR gate pairs.

\* \* \* \* \*